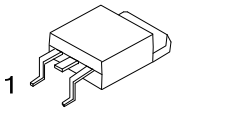
F3N60-LC

Power MOSFET

3.0A, 600V N-CHANNEL POWER MOSFET



TO-252

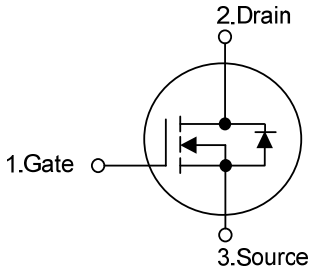
■ DESCRIPTION

The UTC **F3N60-LC** is a N-Channel enhancement mode silicon gate power MOSFET with Fast Body Diode, is designed high voltage, high speed power switching applications such, is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

■ FEATURES

* $R_{DS(ON)} \leq 3.6\ \Omega$ @ V_{GS}=10V, I_D=1.5A
* Fast body diode MOSFET technology
* Fast switching capability
* Avalanche energy tested
* Improved dv/dt capability, high ruggedness

■ SYMBOL



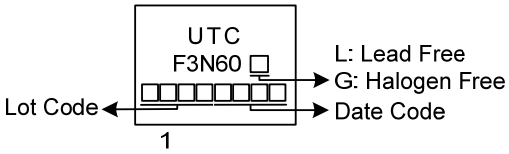
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
F3N60L-TN3-R	F3N60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

F3N60G-TN3-R (1)Packing Type (2)Package Type (3)Green Package	(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_D	3	A
	Pulsed (Note 2)	I_{DM}	6	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	92	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	7.28	V/ns
Power Dissipation		P_D	47	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=30mH, I_{AS}=2.47A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C
4. I_{SD} ≤ 3.0A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	110	°C/W
Junction to Case	θ_{Jc}	2.66 (Note)	°C/W

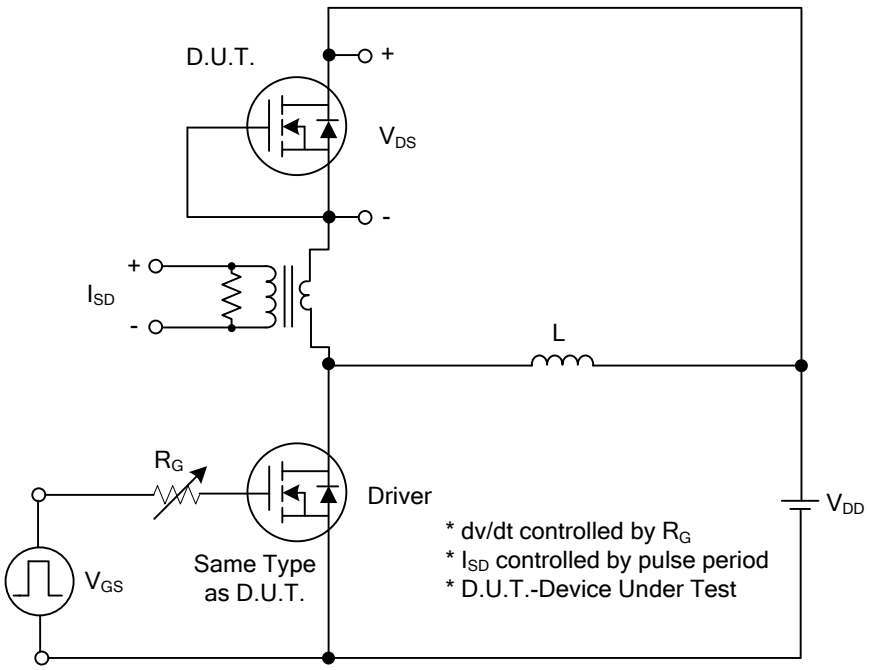
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

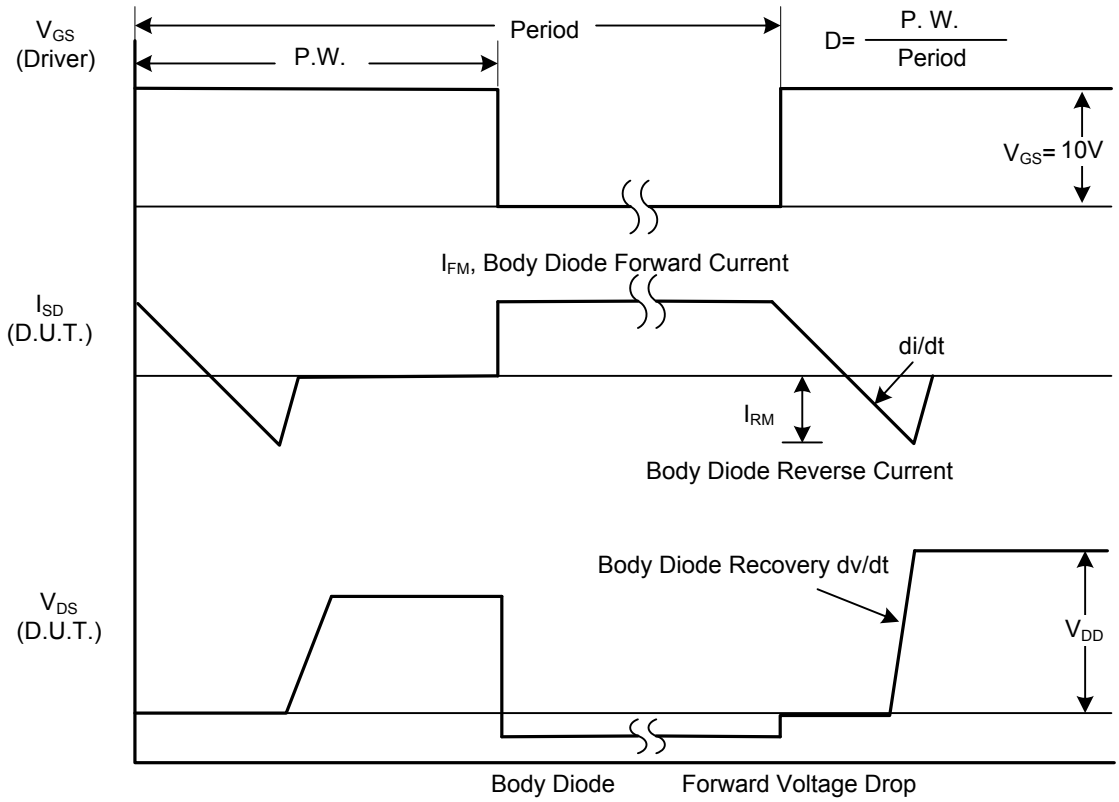
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	600			V
Drain-Source Leakage Current	I_{DSS}	V_{DS} =600V,V_{GS} =0V			10	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Drain to Source On-state Resistance	$R_{DS(ON)}$	V_{GS} =10V, I_D =1.5A			3.6	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		430		pF
Output Capacitance	C_{OSS}			46		pF
Reverse Transfer Capacitance	C_{RSS}			4.5		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q_G	V_{DS}=480V, V_{GS}=10V, I_D=3A, I_G=1mA (Note 1, 2)		14.8		nC
Gate Source Charge	Q_{GS}			5.8		nC
Gate Drain Charge	Q_{GD}			2.06		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=3A, R_G =25Ω (Note 1, 2)		6.4		ns
Turn-ON Rise Time	t_R			16.6		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			34		ns
Turn-OFF Fall-Time	t_F			26		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				3	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				6	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	I_S =3A, V_{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	I_S=3A,V_{GS}=0V, dI/dt=100A/μs		98		ns
Reverse Recovery Charge	Q_{rr}			414		nC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

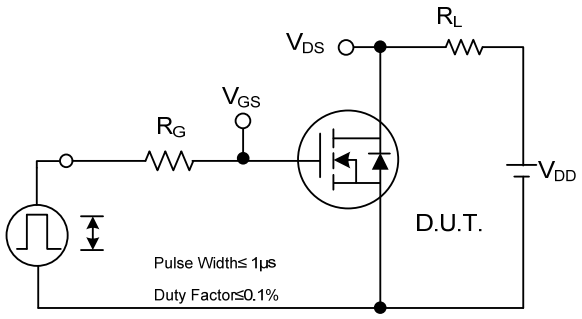


Peak Diode Recovery dv/dt Test Circuit

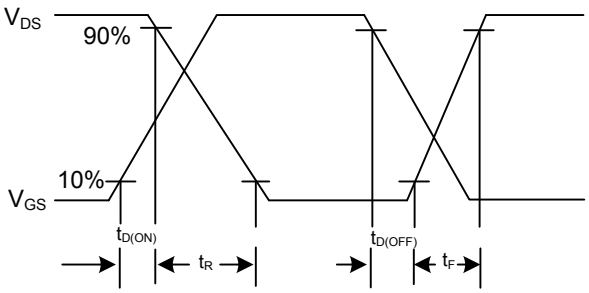


Peak Diode Recovery dv/dt Waveforms

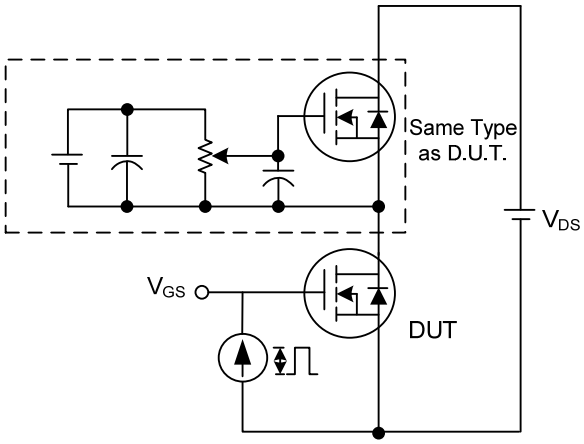
■ TEST CIRCUITS AND WAVEFORMS



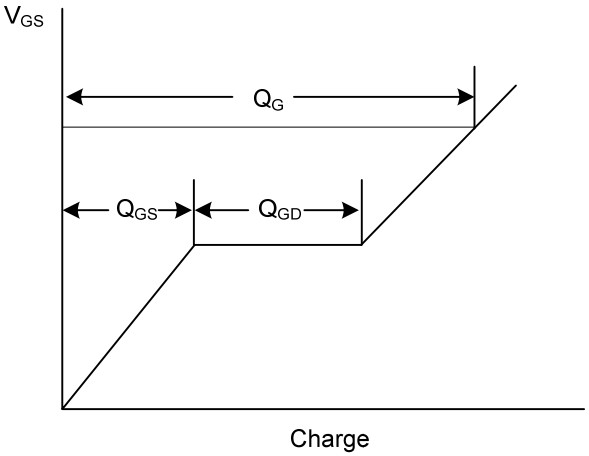
Switching Test Circuit



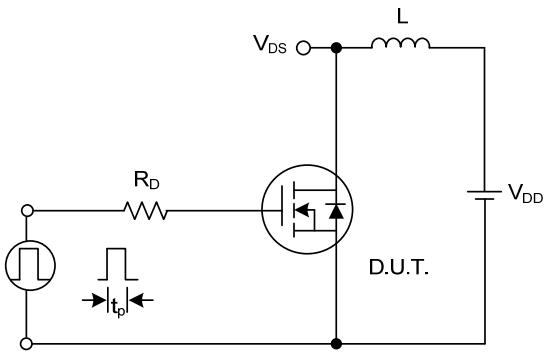
Switching Waveforms



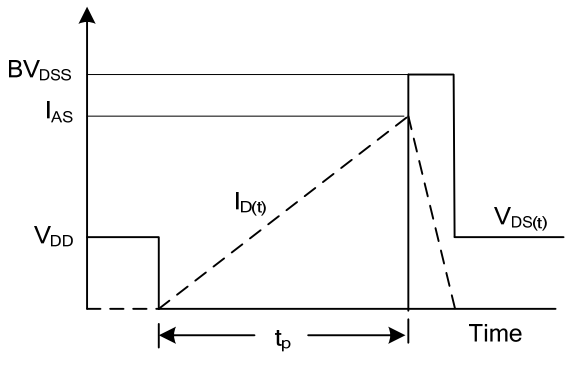
Gate Charge Test Circuit



Gate Charge Waveform



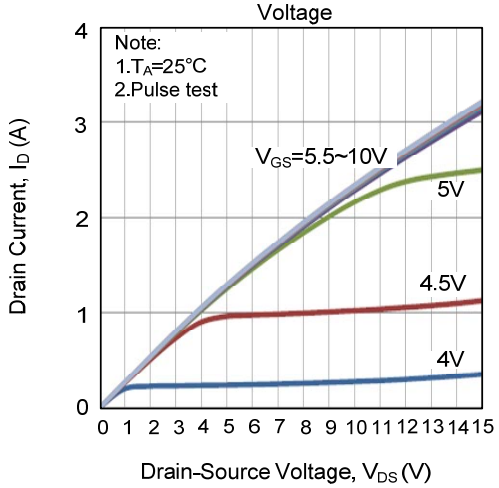
Unclamped Inductive Switching Test Circuit



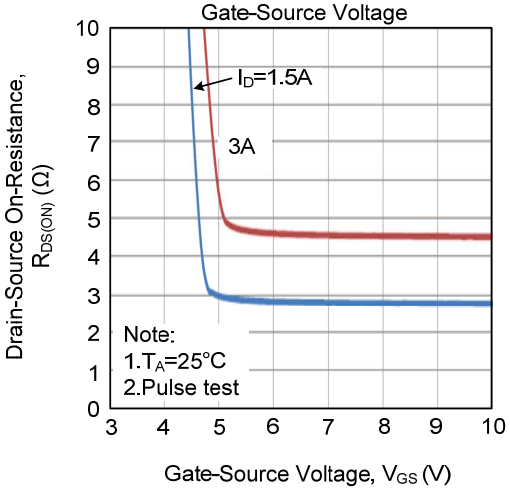
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

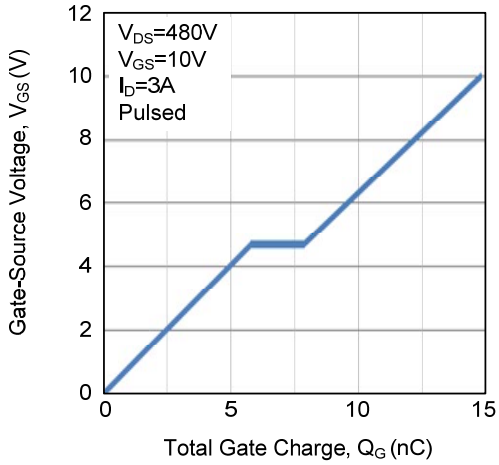
Drain Current vs. Drain-Source Voltage



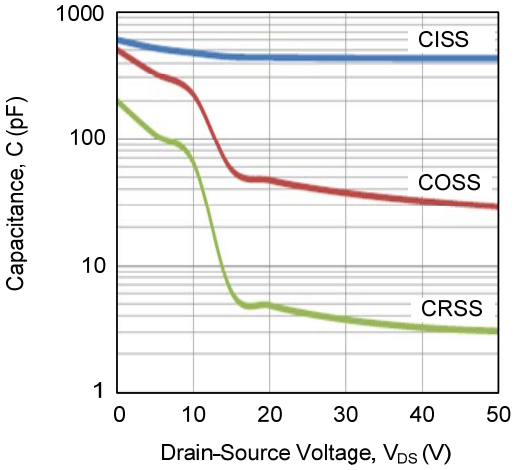
Drain-Source On-Resistance vs. Gate-Source Voltage



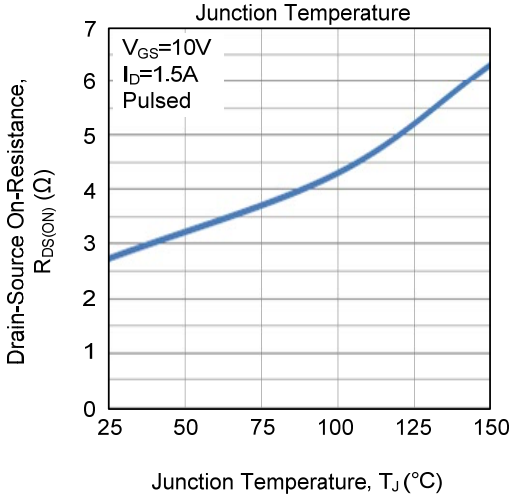
Gate Charge Characteristics



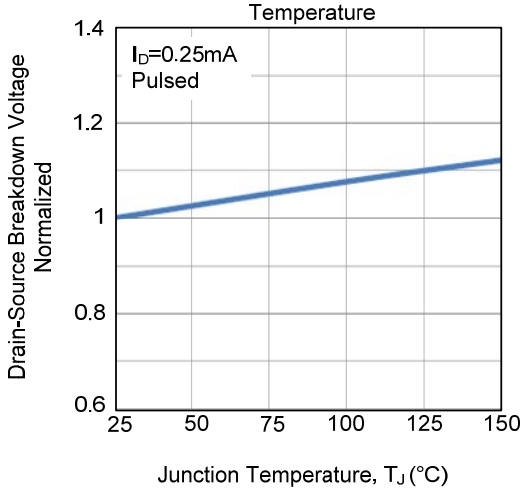
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

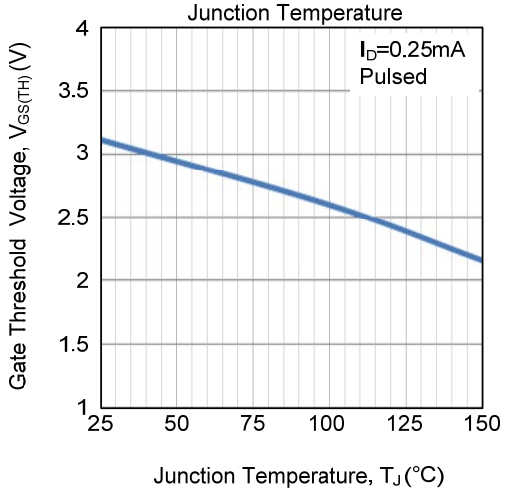


Breakdown Voltage vs. Junction Temperature

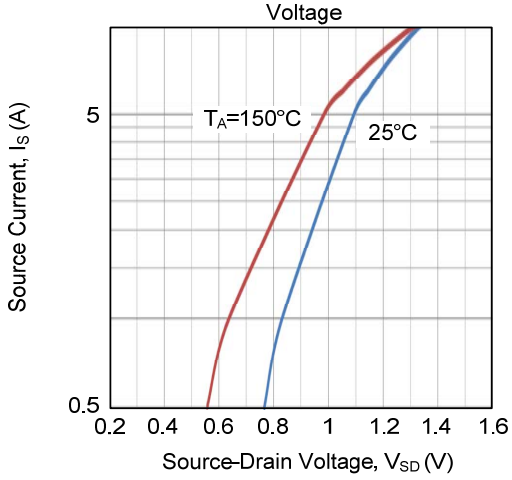


■ TYPICAL CHARACTERISTICS (Cont.)

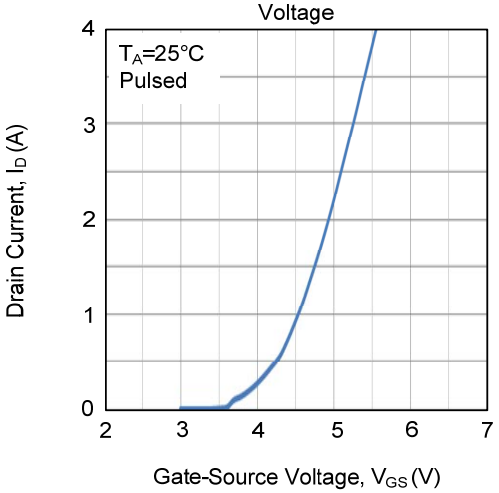
Gate Threshold Voltage vs. Junction Temperature



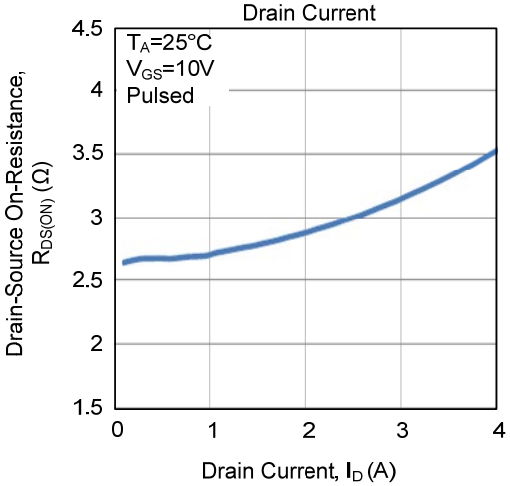
Source Current vs. Source-Drain Voltage



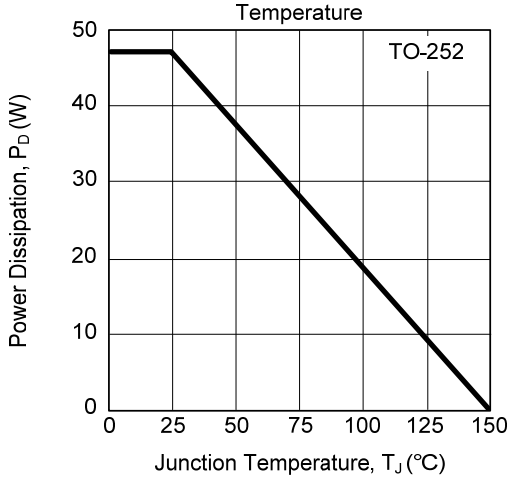
Drain Current vs. Gate-Source Voltage



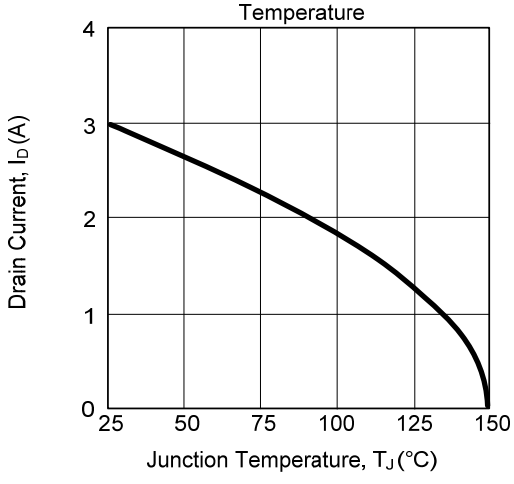
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)